

L Number	Hits	Search Text	DB	Time stamp
4	10	(sic or silicon adj carbide) near2 seed same (boule or ingot) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 10:55
5	39	(sic or silicon adj carbide) near2 seed same diameter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:23
6	9	(sic or silicon adj carbide) near2 seed and (gan or gallium adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:25
8	14	(sic or silicon adj carbide) near2 substrate and (gan or gallium adj nitride) same (ingot or boule)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:30
9	40	(sic or silicon adj carbide) near2 seed and diamond	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:31
10	8	(sic or silicon adj carbide) near2 seed same diamond	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/26 11:31
-	108	((pressure same (vary or varying or varied or varing or alternated or alternating or alternate)) and (sic or silicon adj carbide)) and (117/\$4.ccls. or 427/\$4.ccls.) and (carbon or silicon) near3 source	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 09:44
-	84	((sic or silicon adj carbide) and 117/84-109.ccls.) and source and cycle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 10:01
-	55	((sic or silicon adj carbide) and 117/84-109.ccls.) and puls\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 11:19
-	54	(partial adj pressure) same (silicon or carbon or si or c) and (sic or silicon adj carbide) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 14:33
-	38	(partial adj pressure) same (silicon or carbon) and (sic or silicon adj carbide) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:45
-	28	(sic or silicon adj carbide) same (nnp or pnp) and (438/\$4.ccls. or 117/\$4.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:19
-	8	sccm near10 (silicon or carbon) and (sic or silicon adj carbide) and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 15:54

-	70	(sic or silicon adj carbide) near3 seed and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 16:02
-	13	attach\$4 near3 coefficient and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 09:35
-	54	((sic or silicon adj carbide) and 117/84-109.ccls.) and flow adj rate same (silicon or carbon) same (carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/21 17:39
-	37	attach\$4 near3 coefficient and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 09:54
-	9	attach\$4 adj coefficient and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 11:58
-	18	superlattice same (sic or silicon adj carbide) same dop\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 17:36
-	16	superlattice same (sic or silicon adj carbide) and cycle	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/10/22 15:04
-	80	superlattice same (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/21 17:46
-	46	(ald or ale or atomic adj layer adj (epitax\$4 or deposit\$4)) same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 09:40
-	38	attachment near2 coefficient same (gas\$4 or pressure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:01
-	11	attachment near2 coefficient and (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:05
-	4	attachment near2 coefficient same (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 10:12
-	20	((constant\$4 or stead\$4) near3 (gas or reactant or pressure or flow) same (sic or silicon adj carbide)) and puls\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:06
-	17	117/84-109.ccls. and (silicon adj carbide or sic) and puls\$4 near3 deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/22 11:11

-	11	117/84-109.ccls. and puls\$4 near3 deposit\$4 not laser	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 11:53
-	22	(sic or silicon adj carbide) same (vapor adj deposit\$4) same puls\$4	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:14
-	19	(vapor adj deposit\$4) near2 puls\$4 and (constant\$4 or continuous\$4 or stead\$4) near4 (flow\$4 or gas\$4 or react\$4)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:25
-	7	(vapor adj deposit\$4) near2 puls\$4 and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:27
-	3	puls\$4 same (silicon adj carbide or sic) not laser and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:38
-	17	puls\$4 near3 (deposit\$4 or growth) and superlattice and 117/84-109.ccls.	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:42
-	14	puls\$4 near3 (deposit\$4 or growth) and superlattice not laser	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:28
-	13	puls\$4 near3 (reactant) and (stead\$4 or continuous\$4 or constant\$4) near3 (reactant)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/25 13:45
-	6	(si or silicon) near2 (sic or silicon adj carbide) same superlattice	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:16
-	20	(si or silicon) near2 (sic or silicon adj carbide) and (((si or silicon) near3 (reactant or source or gas) and (carbon) near2 (reactant or source)) same (puls\$4 or continuous\$4 or stead\$4))	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:24
-	36	(silicon or si or carbon) near3 puls\$4 and (silicon adj carbide or sic) not laser	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:36
-	10	puls\$4 near3 deposition same superlattice	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:39
-	7	puls\$4 near3 deposition and superlattice not laser	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:41
-	6	superlattice same (silicon or si) near2 (silicon adj carbide or sic)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TDB	2002/11/22 13:44

-	51	(silicon adj carbide or sic) same puls\$4 same deposit\$4 not laser	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/22 16:13
-	32	(silicon adj carbide or sic) same (deposit\$4) and (silicon or si near3 (partial adj pressure)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/22 16:14
-	3	((carbon or silicon or si) near2 (stead\$4 or continuous\$4 or constant\$4) near2 (flow or pressure)) and (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 11:10
-	9	(silicon adj carbide or sic) same (vapor adj phase adj epitaxy or sublimation adj recrystallization or liquid adj deposition) same bulk	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 13:47
-	8	(silicon adj carbide or sic) adj bulk and (vapor adj phase adj epitaxy or sublimation adj recrystallization or liquid adj deposition)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 13:51
-	92	(silicon adj carbide or sic) same (low adj pressure same CVD)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 13:57
-	14	(silicon adj carbide or sic) same (low adj pressure same CVD) and growth adj rate	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 14:28
-	89	(silicon adj carbide or sic) same (CVD) and growth adj rate same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 14:40
-	35	(CVD) same growth adj rate same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 15:04
-	9	(sic or silicon adj carbide) near2 seed same (gan or gallium adj nitride or diamond)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 15:09
-	3	(sic or silicon adj carbide) near2 seed and (gan or gallium adj nitride or diamond) same CVD	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 15:24
-	19	dop\$4 same superlattice same (sic or silicon adj carbide)	USPAT; US-PGPUB; EPO; JPO; DEFWENT; IBM_TLB	2002/11/25 17:09